

In some embodiments, at least a portion of the mechanical layer 732 is electrically conductive and comprises the second electrode in the MEMS device 700. In certain embodiments, portions of the support posts 736a and 736b are electrically nonconductive and insulate portions of the mechanical layer 732 from other portions of the device 700 (e.g., the optical layer 724).

[0121] The MEMS device 700 shown in FIG. 14 comprises electrodes 756a and 756b that are disposed above the support posts 736a and 736b and that are electrically insulated from other portions of the device 700 by electrically nonconductive regions 758a and 758b. In some embodiments, the electrically nonconductive regions 758a, 758b comprise a dielectric material such as, for example, a dielectric film. In the embodiment shown in FIG. 14, the third electrode 103 comprises the electrodes 756a and 756b. The electrodes 756a and 756b in other embodiments can have shapes and sizes that are different than shown in FIG. 14. For example, the electrodes 756a and 756b may be relatively short in some embodiments. It is preferred, although not necessary, for at least a portion of each of the electrodes 756a and 756b to be disposed above at least a portion of the reflective element 107.

[0122] FIG. 14 schematically illustrates the MEMS device 700 when the reflective element 107 is in a first position (the actuated or driven state) in which the reflective element 107 is in contact with a portion 113 of the device 700. As further described above, the reflective element 107 can move to a second position (the unactuated or relaxed state) in which it is not in contact with the portion 113. For example, the mechanical layer 732 may be fabricated from a mechanically deformable material such as a metal (e.g., aluminum) that can move between the first and second positions. When the device 700 is in the driven state, the mechanical layer 732 is deformed and comprises bending regions 760a and 760b, which are disposed between the portion 113 and the support posts 736a and 736b, respectively. In certain embodiments, the reflective element 107 (when in the driven state) is also deformed and also comprises the bending regions 760a and 760b.

[0123] In some embodiments of the device 700, at least portions of the electrodes 756a and 756b are disposed higher than the reflective element 107 when the reflective element 107 is in the first position. In certain embodiments, at least a portion of each of the electrodes 756a and 756b protrudes away from the support posts 736a and 736b, respectively, such that these portions are disposed above (e.g., higher than) at least a portion of the reflective element 107 when the reflective element 107 is in the first position (FIG. 14). In certain preferred embodiments, the electrodes 756a and 756b are configured so that at least a portion of the electrodes 756a and 756b is disposed directly above at least a portion of the bending regions 760a and 760b, respectively.

[0124] In some embodiments of the MEMS device 700, voltages are applied to the electrodes 101, 102, and 103 so that a net electrostatic force on the reflective element 107 at least partially reduces or counteracts the adhesive force on the reflective element 107 in the first position. As discussed further above, the voltages may have various ranges of magnitudes and frequencies and may be applied to induce displacements, oscillations, and/or vibrations of the reflective element 107 to assist in moving the reflective element 107 from the first position to the second position. In certain embodiments, a voltage difference is applied between the

third electrode 103 (e.g., the electrodes 756a, 756b) and the second electrode 102 (e.g., an electrically conductive portion of the mechanical layer 732). The voltage difference can have various ranges of magnitudes and frequencies and can comprise one or more relatively short duration impulses. In various embodiments, the third electrode 103 is electrically connected to one or more voltage sources by traces or wires that lead off of the display array 30 to the array driver 22 (see FIG. 2). In one embodiment of the device 700, the array driver 22 may use a driver circuit generally similar to the row and column driver circuits 24 and 26 to communicate a suitable electrical signal to the third electrode 103.

[0125] The voltage difference applied between the second and third electrodes 102 and 103 causes net electrostatic forces indicated by arrows 764a and 764b to act on the reflective element 107. In certain preferred embodiments, portions of the electrodes 756a and 756b protrude directly above at least portions of the bending regions 760a and 760b so that the net electrostatic forces 764a and 764b have reasonably large perpendicular components in the bending regions 760a and 760b that tend to pull the reflective element 107 away from the portion 113. In certain such embodiments, the electrostatic forces 764a and 764b may at least partially reduce or counteract the adhesive force and may assist in moving the reflective element 107 from the first position to the second position. Without subscribing to any particular theory, the net electrostatic force 764a applied in the bending region 760a may induce crack opening at an edge of a contact interface between the reflective element 107 and the portion 113. The crack may propagate across the contact interface, assisting the reflective element 107 to peel away from the portion 113 and to move from the first position to the second position. The net electrostatic force 764b applied in the bending region 760b may act in a similar manner, and in certain embodiments cracks may open at opposing edges of the contact interface and propagate across the interface. Although it is preferred that at least two electrodes 756a and 756b be used to reduce or counteract the adhesive force on the reflective element 107, in other embodiments different configurations, orientations, and numbers of electrodes (e.g., one) can be used, for example, to initiate crack opening and facilitate release of the reflective element 107.

[0126] Embodiments of the MEMS device 700 can provide certain advantages. For example, the magnitudes of the electrostatic forces 764a, 764b at the bending regions 760a, 760b needed to facilitate release from the driven to the undriven state typically are much smaller than if the forces were applied to a central region of the reflective element 107. Accordingly, smaller voltage differences (e.g., between the second and third electrodes 102 and 103) can be applied to the device 700. Moreover, in some embodiments, the electrodes 756a and 756b reduce electrostatic instability and collapse of the mechanical layer 732 onto the dielectric layer 728, which can be a problem in some closing-gap devices. Further, in certain embodiments, voltage impulses having a duration that is shorter than a typical release time of the device 700 can be used to facilitate movement of the reflective element 107 from the driven state to the undriven state.

[0127] The MEMS devices disclosed herein may be fabricated using suitable micromachining processes such as, for example, selective deposition and etching as described in the heretofore incorporated U.S. patent application Ser. No.